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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Active
Number of LABs/CLBs	7911
Number of Logic Elements/Cells	101261
Total RAM Bits	4939776
Number of I/O	326
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc6slx100-2fgg484c

Table 3: eFUSE Programming Conditions⁽¹⁾

Symbol	Description	Min	Typ	Max	Units
V_{FS} ⁽²⁾	External voltage supply	3.2	3.3	3.4	V
I_{FS}	V_{FS} supply current	–	–	40	mA
V_{CCAUX}	Auxiliary supply voltage relative to GND	3.2	3.3	3.45	V
R_{FUSE} ⁽³⁾	External resistor from R_{FUSE} pin to GND	1129	1140	1151	Ω
V_{CCINT}	Internal supply voltage relative to GND	1.14	1.2	1.26	V
t_j	Temperature range	15	–	85	$^{\circ}\text{C}$

Notes:

1. These specifications apply during programming of the eFUSE AES key. Programming is only supported through JTAG. The AES key is only supported in the following devices: LX75, LX75T, LX100, LX100T, LX150, and LX150T.
2. When programming eFUSE, V_{FS} must be less than or equal to V_{CCAUX} . When not programming or when eFUSE is not used, Xilinx recommends connecting V_{FS} to GND. However, V_{FS} can be between GND and 3.45 V.
3. An R_{FUSE} resistor is required when programming the eFUSE AES key. When not programming or when eFUSE is not used, Xilinx recommends connecting the R_{FUSE} pin to V_{CCAUX} or GND. However, R_{FUSE} can be unconnected.

Table 14: GTP Transceiver Current Supply (per Lane)

Symbol	Description	Typ ⁽¹⁾	Max	Units
$I_{MGTAVCC}$	GTP transceiver internal analog supply current	40.4	Note 2	mA
$I_{MGTAVTTX}$	GTP transmitter termination supply current	27.4		mA
$I_{MGTAVTRX}$	GTP receiver termination supply current	13.6		mA
$I_{MGTAVCCPLL}$	GTP transmitter and receiver PLL supply current	28.7		mA
$R_{MGTRREF}$	Precision reference resistor for internal calibration termination	$50.0 \pm 1\%$ tolerance		Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C, with a 2.5 Gb/s line rate, with a shared PLL use mode.
2. Values for currents of other transceiver configurations and conditions can be obtained by using the XPOWER Estimator (XPE) or XPOWER Analyzer (XPA) tools.

Table 15: GTP Transceiver Quiescent Supply Current (per Lane)⁽¹⁾⁽²⁾⁽³⁾⁽⁴⁾

Symbol	Description	Typ ⁽⁵⁾	Max	Units
$I_{MGTAVCCQ}$	Quiescent MGTAVCC supply current	1.7	Note 2	mA
$I_{MGTAVTTXQ}$	Quiescent MGTAVTTX supply current	0.1		mA
$I_{MGTAVTRXQ}$	Quiescent MGTAVTRX supply current	1.2		mA
$I_{MGTAVCCPLQ}$	Quiescent MGTAVCCPLL supply current	1.0		mA

Notes:

1. Device powered and unconfigured.
2. Currents for conditions other than values specified in this table can be obtained by using the XPOWER Estimator (XPE) or XPOWER Analyzer (XPA) tools.
3. GTP transceiver quiescent supply current for an entire device can be calculated by multiplying the values in this table by the number of available GTP transceivers.
4. Does not include power-up MGTAVTTRCAL supply current during device configuration.
5. Typical values are specified at nominal voltage, 25°C.

